



Features

- Low forward voltage drop
- High reverse voltage
- Hermetic metal cases with ceramic insulators

Typical Applications

- All purpose high power rectifier diodes
- High power resistance welding equipment
- Non-controllable and half-controllable rectifiers
- Controlled rectifiers

Part No. H125ZPR-ZT110c(d)T

I_{F(AV)}	5250A
V_{RRM}	5200V 5600V 6000V 6500V

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _J (°C)	VALUE			UNIT
				Min	Type	Max	
I _{F(AV)}	Mean forward current	180° half sine wave 50Hz Double side cooled, T _C =100°C	150			5250	A
V _{RRM}	Repetitive peak reverse voltage	tp=10ms	150	5100		6500	V
I _{RRM}	Repetitive peak current	at V _{RRM}	150			400	mA
I _{FSM}	Surge forward current	10ms half sine wave	150			84	kA
I ² t	I ² t for fusing coordination	V _R =0.6V _{RRM}					35280
V _{FO}	Threshold voltage		150			0.81	V
r _F	Forward slope resistance						0.12
V _{FM}	Peak forward voltage	I _{FM} =5000A, F=140kN	25			1.65	V
Q _{rr}	Recovery charge	I _{FM} =2000A, tp=4000μs, di/dt=-20A/μs, V _R =100V	150		20000		μC
R _{th(j-c)}	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force140kN				0.004	°C /W
R _{th(c-h)}	Thermal resistance case to heat sink					0.001	
F _m	Mounting force			110		140	kN
T _{vj}	Junction temperature			-40		150	°C
T _{stg}	Stored temperature			-40		160	°C
W _t	Weight					3420	g
Outline	ZT110cT/ ZT110dT						

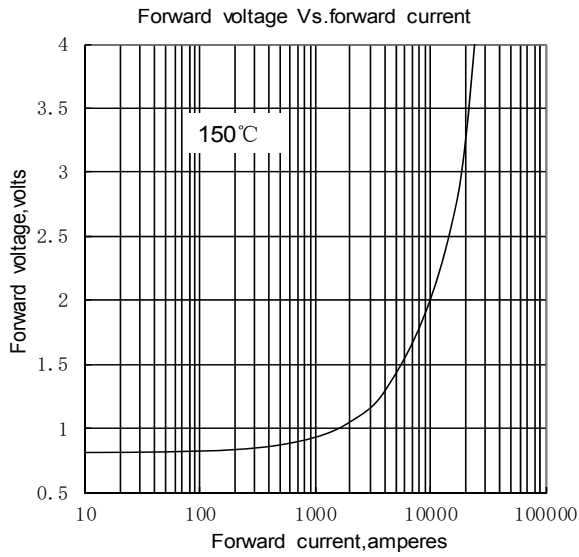


Fig.1

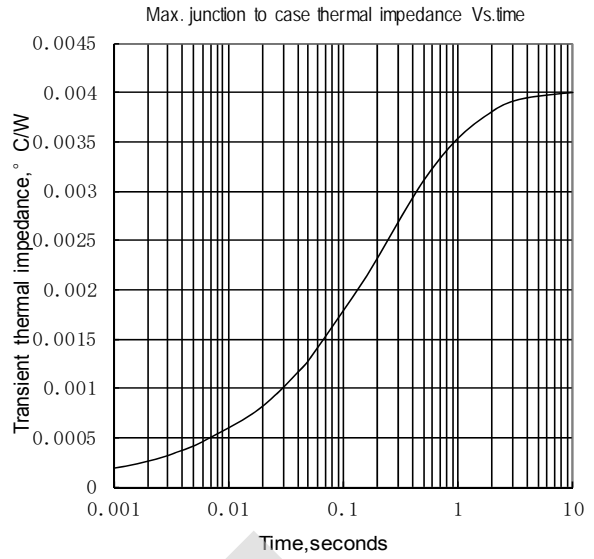


Fig.2

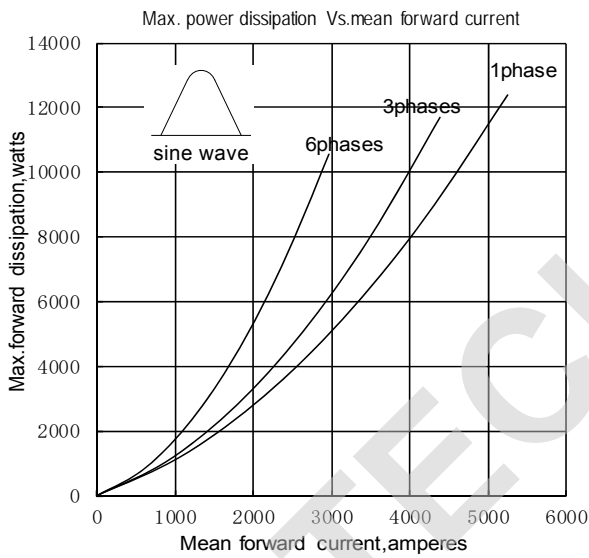


Fig.3

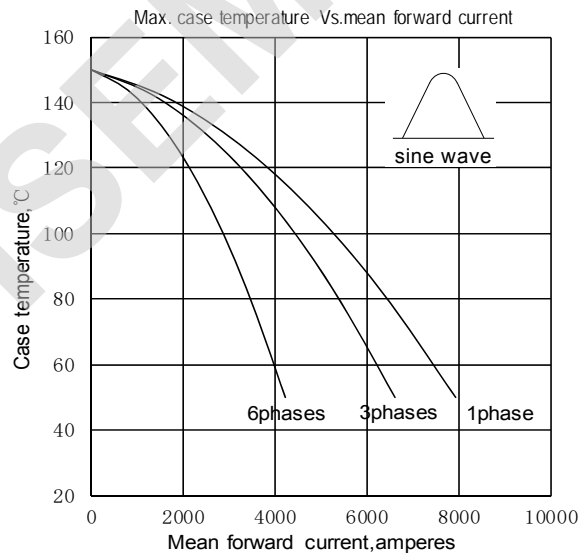


Fig.4

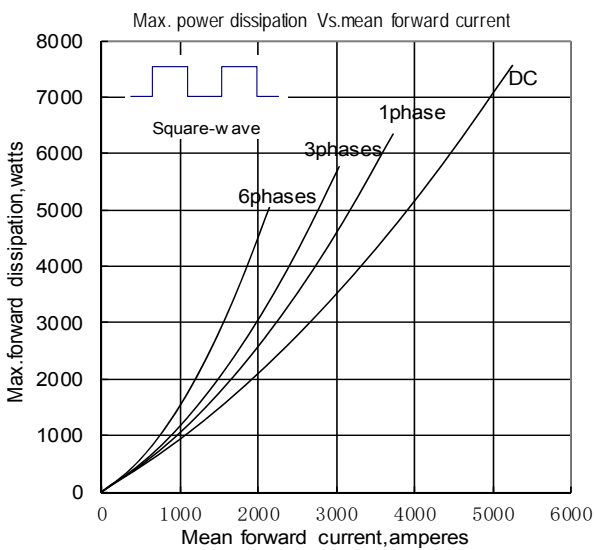


Fig.5

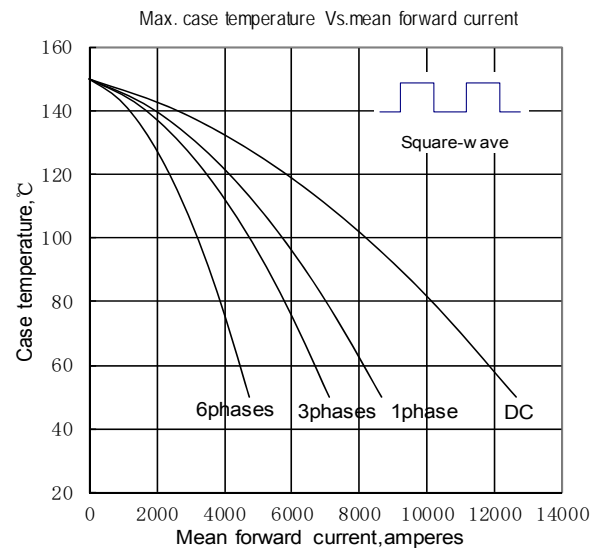


Fig.6

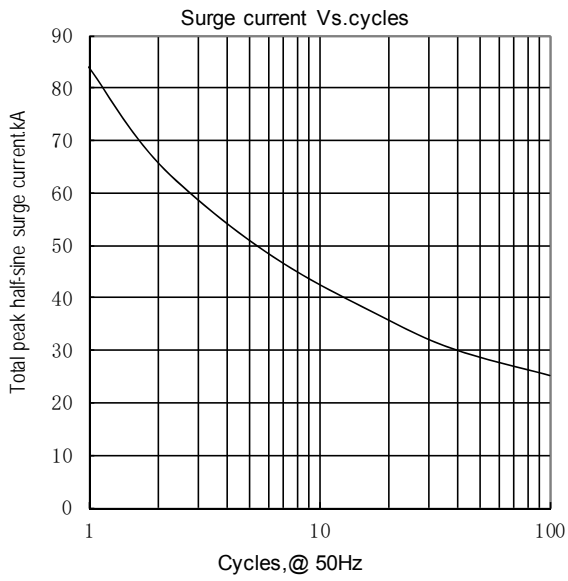


Fig.7

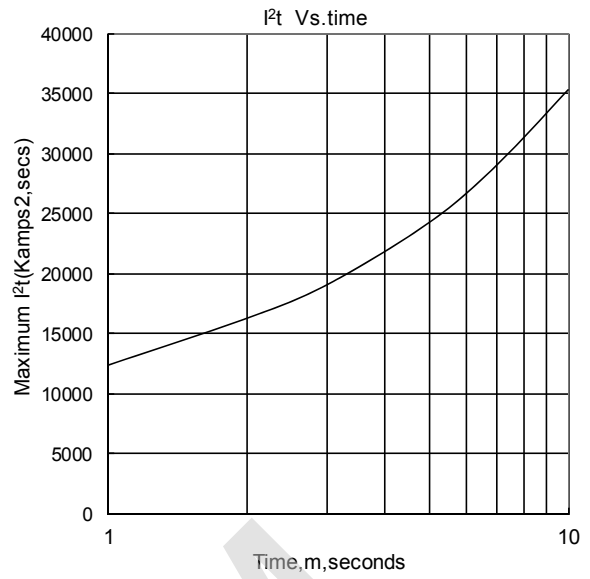
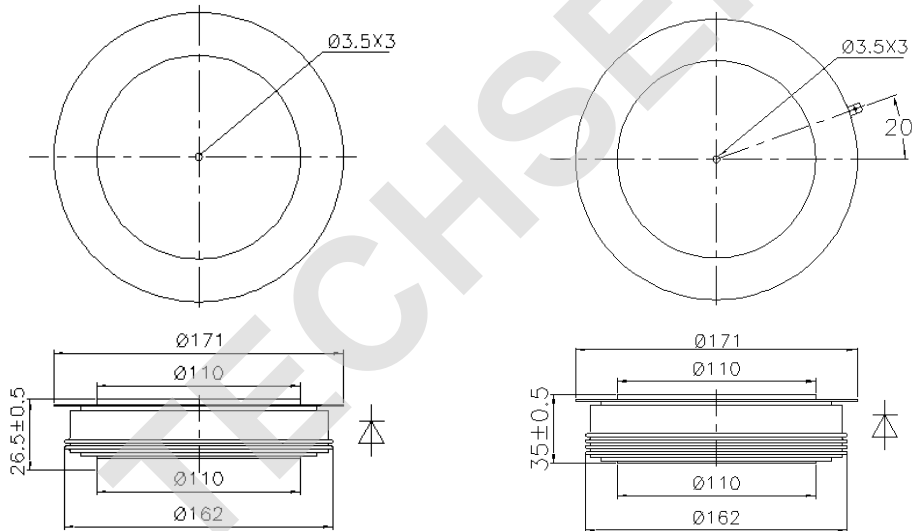


Fig.8

Outline:



TECHSEM reserves the right to change specifications without notice.